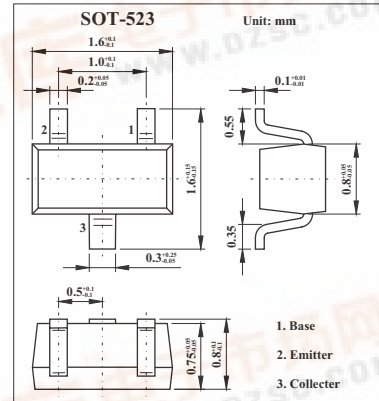


SMD Type Transistors

Silicon PNP Epitaxial Type Transistor  
2SA1832

Features

- High Voltage and High Current : $V_{CE0}=-50V, I_C=-150mA$ (Max.)
- Excellent hFE Linearity :  
 $hFE(I_C=-0.1mA) / hFE(I_C=-2mA)=0.95$ (Typ.)
- High hFE:  $hFE=70$  to 400



Absolute Maximum Ratings  $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-50	V
Collector-emitter voltage	$V_{CE0}$	-50	V
Emitter-base voltage	$V_{EB0}$	-5	V
Collector current	$I_C$	-150	mA
Base current	$I_B$	-30	mA
Collector power dissipation	$P_C$	100	mW
Junction temperature	$T_j$	125	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ C$

Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector cutoff current	$I_{CB0}$	$V_{CB} = -5V, I_E = 0$			-0.1	$\mu A$
Emitter cutoff current	$I_{EB0}$	$V_{EB} = -5V, I_C = 0$			-0.1	$\mu A$
DC current Gain	hFE	$V_{CE} = -6V, I_C = -2mA$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$		-0.1	-0.3	V
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		4	7	pF
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -1mA$	80			MHz

hFE Classification

Marking	SQ	SY	SG
Rank	Q	Y	GR
hFE	70~140	120~240	200~400

